Nuclear Instruments and Methods in Physics Research B 175–177 (2001) 802–817

ELSEVIER

NIM B
Beam Interactions with Materials & Atoms

www.elsevier.nl/locate/nimb

Author index

Abramof, E., see Beloto, A.F. 175–177 (2001) 224
Abramof, E., A.F. Beloto, M. Ueda, R. Günzel and H. Reuther, Reciprocal space mapping of silicon implanted with nitrogen by plasma immersion ion implantation 175–177 (2001) 229
Abramof, E., see Ueda, M. 175–177 (2001) 715
Achete, C.A., see Castro Vidaurre, E.F. 175–177 (2001) 732
Added, N., J.F.D. Chubaci, M. Matsuoka, R.A. Castro, M. Radtke, E. Alonso, R. Liguori Neto, M.A. Rizzuto, M. Tabacniks and R.D. Mansano, Light element analysis using ERDA method with an ionization chamber 175–177 (2001) 787
Adriaenssens, G.J., see Vantomme, A. 175–177 (2001) 148
Aguirre, M.H. and H.R. Cánepa, Ar-implanted epitaxially grown HgCdTe: evaluation of structural damage by RBS and TEM 175–177 (2001) 274
Akiyama, H., see Nakashima, K. 175–177 (2001) 208
Alonso, E., see Added, N. 175–177 (2001) 787
Alves, E., see Barradas, N.P. 175–177 (2001) 108
Alves, E., C. Liu, J.C. Waerenborgh, M.F. da Silva and J.C. Soares, Study of Fe^+ implanted GaN 175–177 (2001) 241
Alves, E., see Marques, C. 175–177 (2001) 500
Alves, M.C.M., see Borges, J.F.M. 175–177 (2001) 485
Amaral, L., see Kling, A. 175–177 (2001) 331
Amaral, L., see Kling, A. 175–177 (2001) 394
Amaral, L., see Heyden, D. 175–177 (2001) 403
Amaral, L., see Motta, A.T. 175–177 (2001) 521
Amaral, L., see Moura, C.S. 175–177 (2001) 526
Amekura, H., N. Umeda, N. Okubo, C.G. Lee, Y. Takeda and N. Kishimoto, Microstructural changes in silicon thermal oxide induced by high-flux copper negative-ion implantation 175–177 (2001) 345
Amekura, H., see Okubo, N. 175–177 (2001) 663
Andrienko, I., see Jamieson, D.N. 175–177 (2001) 744
Angilella, G.G.N., see Compagnini, G. 175–177 (2001) 559
Antunes, A.B., see Heck, C. 175–177 (2001) 296
Anwand, W., see Fradin, J. 175–177 (2001) 516
Aono, K., H. Toida, K. Terashima and M. Iwaki, Annealing effects on luminescence from Ce-implanted α-Al_2O_3 ..... 175–177 (2001) 580
Araújo, J.P., see Wahl, U. 175–177 (2001) 262
Artús, L., see Ibáñez, J. 175–177 (2001) 246
Artús, L., see Marcos, B. 175–177 (2001) 252
Auret, D., see Vantomme, A. 175–177 (2001) 148
Auret, F.D., S.A. Goodman, M. Hayes, M.J. Legodi, S.S. Hullavarad, E. Friedland, B. Beaumont and P. Gibart, Electrical characterisation of epitaxially grown n-GaN bombarded with high- and low-energy protons 175–177 (2001) 292
Azevedo, G. de M., see da Silva, D.L. 175–177 (2001) 98

Baibich, M.N., see Heck, C. 175–177 (2001) 296
Balogh, A.G., see Nagel, R. 175–177 (2001) 398
Balzaretti, N.M., see Soares, S.R.S. 175–177 (2001) 474
Bandourko, V., T.T. Lay, Y. Takeda, C.G. Lee and N. Kishimoto, Ion-induced photon emission of magnesium aluminate spinel during 60 keV Cu^- implantation 175–177 (2001) 68
Baptista, D.L., see Lopes, J.M.J. 175–177 (2001) 673
Barbour, J.C., J.W. Braithwaite and A.F. Wright, Determination of solid-state sulfidation mechanisms in ion-implanted copper 175–177 (2001) 382

0168-583X/01/$ - see front matter © 2001 Published by Elsevier Science B.V. All rights reserved.
PII: S0168-583X(01)00586-9

Nuclear Instruments and Methods in Physics Research B 175–177 (2001) 802–817

ELSEVIER

NIM B
Beam Interactions with Materials & Atoms

www.elsevier.nl/locate/nimb

Author index

Abramof, E., see Beloto, A.F. 175–177 (2001) 224
Abramof, E., A.F. Beloto, M. Ueda, R. Günzel and H. Reuther, Reciprocal space mapping of silicon implanted with nitrogen by plasma immersion ion implantation 175–177 (2001) 229
Abramof, E., see Ueda, M. 175–177 (2001) 715
Achete, C.A., see Castro Vidaurre, E.F. 175–177 (2001) 732
Added, N., J.F.D. Chubaci, M. Matsuoka, R.A. Castro, M. Radtke, E. Alonso, R. Liguori Neto, M.A. Rizzuto, M. Tabacniks and R.D. Mansano, Light element analysis using ERDA method with an ionization chamber 175–177 (2001) 787
Adriaenssens, G.J., see Vantomme, A. 175–177 (2001) 148
Aguirre, M.H. and H.R. Cánepa, Ar-implanted epitaxially grown HgCdTe: evaluation of structural damage by RBS and TEM 175–177 (2001) 274
Akiyama, H., see Nakashima, K. 175–177 (2001) 208
Alonso, E., see Added, N. 175–177 (2001) 787
Alves, E., see Barradas, N.P. 175–177 (2001) 108
Alves, E., C. Liu, J.C. Waerenborgh, M.F. da Silva and J.C. Soares, Study of Fe^+ implanted GaN 175–177 (2001) 241
Alves, E., see Marques, C. 175–177 (2001) 500
Alves, M.C.M., see Borges, J.F.M. 175–177 (2001) 485
Amaral, L., see Kling, A. 175–177 (2001) 331
Amaral, L., see Kling, A. 175–177 (2001) 394
Amaral, L., see Heyden, D. 175–177 (2001) 403
Amaral, L., see Motta, A.T. 175–177 (2001) 521
Amaral, L., see Moura, C.S. 175–177 (2001) 526
Amekura, H., N. Umeda, N. Okubo, C.G. Lee, Y. Takeda and N. Kishimoto, Microstructural changes in silicon thermal oxide induced by high-flux copper negative-ion implantation 175–177 (2001) 345
Amekura, H., see Okubo, N. 175–177 (2001) 663
Andrienko, I., see Jamieson, D.N. 175–177 (2001) 744
Angilella, G.G.N., see Compagnini, G. 175–177 (2001) 559
Antunes, A.B., see Heck, C. 175–177 (2001) 296
Anwand, W., see Fradin, J. 175–177 (2001) 516
Aono, K., H. Toida, K. Terashima and M. Iwaki, Annealing effects on luminescence from Ce-implanted α-Al_2O_3 ..... 175–177 (2001) 580
Araújo, J.P., see Wahl, U. 175–177 (2001) 262
Artús, L., see Ibáñez, J. 175–177 (2001) 246
Artús, L., see Marcos, B. 175–177 (2001) 252
Auret, D., see Vantomme, A. 175–177 (2001) 148
Auret, F.D., S.A. Goodman, M. Hayes, M.J. Legodi, S.S. Hullavarad, E. Friedland, B. Beaumont and P. Gibart, Electrical characterisation of epitaxially grown n-GaN bombarded with high- and low-energy protons 175–177 (2001) 292
Azevedo, G. de M., see da Silva, D.L. 175–177 (2001) 98

Baibich, M.N., see Heck, C. 175–177 (2001) 296
Balogh, A.G., see Nagel, R. 175–177 (2001) 398
Balzaretti, N.M., see Soares, S.R.S. 175–177 (2001) 474
Bandourko, V., T.T. Lay, Y. Takeda, C.G. Lee and N. Kishimoto, Ion-induced photon emission of magnesium aluminate spinel during 60 keV Cu^- implantation 175–177 (2001) 68
Baptista, D.L., see Lopes, J.M.J. 175–177 (2001) 673
Barbour, J.C., J.W. Braithwaite and A.F. Wright, Determination of solid-state sulfidation mechanisms in ion-implanted copper 175–177 (2001) 382

0168-583X/01/$ - see front matter © 2001 Published by Elsevier Science B.V. All rights reserved.
PII: S0168-583X(01)00586-9

Barcz, A., see Werner, Z. 175–177 (2001) 767
Barradas, N.P., A. Vieira and E. Alves, Artificial neural network analysis of RBS data of Er-implanted sapphire 175–177 (2001) 108
Battaglin, G., E. Cattaruzza, C. de Julian Fernandez, G. De Marchi, F. Gonella, G. Mattei, C. Maurizio, P. Mazzoldi, A. Miotello, C. Sada and F. D'Acapito, Influence of post-implantation thermal and laser annealing on the stability of metal–alloy nanoclusters in silica 175–177 (2001) 410
Battaglin, G., see de Julián Fernández, C. 175–177 (2001) 479
Baumvol, I.J.R., see Krug, C. 175–177 (2001) 694
Baumvol, I.J.R., see Krug, C. 175–177 (2001) 705
Baumvol, I.J.R., see da Rosa, E.B.O. 175–177 (2001) 762
Beaumont, B., see Auret, F.D. 175–177 (2001) 292
Behar, M., see de Souza, J.P. 175–177 (2001) 46
Behar, M., see da Silva, D.L. 175–177 (2001) 98
Behar, M., see Peeva, A. 175–177 (2001) 176
Behar, M., see da Silva, D.L. 175–177 (2001) 335
Behar, M., see Heyden, D. 175–177 (2001) 403
Beloto, A.F., M. Ueda, E. Abramof, J.R. Senna, N.F. Leite, M.D. da Silva and H. Reuther, Porous silicon implanted with nitrogen by plasma immersion ion implantation 175–177 (2001) 224
Beloto, A.F., see Abramof, E. 175–177 (2001) 229
Beloto, A.F., see Ueda, M. 175–177 (2001) 715
Benyagoub, A., F. Couvreur, S. Bouffard, F. Levesque, C. Dufour and E. Paumier, Phase transformation induced in pure zirconia by high energy heavy ion irradiation 175–177 (2001) 417
Benyagoub, A., see Boccanfuso, M. 175–177 (2001) 590
Berger, A., see Ecker, K.H. 175–177 (2001) 797
Bernas, H., see Devolder, T. 175–177 (2001) 375
Berni, L.A., see Ueda, M. 175–177 (2001) 715
Birtcher, R.C., J. Matsuo and I. Yamada, Craters produced on Al, Cu and Au by Ar cluster impacts 175–177 (2001) 36
Birtcher, R.C., S.E. Donnelly, L.E. Rehn and L. Thomé, Nanocluster formation during ion irradiation of $SiO_2/Ag/SiO_2$ multilayers 175–177 (2001) 40
Birtcher, R.C., see Donnelly, S.E. 175–177 (2001) 132
Birtcher, R.C., see Motta, A.T. 175–177 (2001) 521
Blando, E., E.K. Tentardini and R. Hübler, Microhardness characterization of multilayers modified by ion beam mixing 175–177 (2001) 620
Blando, E., see Tentardini, E.K. 175–177 (2001) 626
Boccanfuso, M., A. Benyagoub, M. Toulemonde, C. Trautmann, K. Schwartz and Ch. Dufour, Heavy-ion induced damage in fluorite nanopowder 175–177 (2001) 590
Bolduc, M., D. Popovici and B. Terreault, Giant segregation effect and surface mechanical modification of aluminum alloys by oxygen plasma source ion implantation 175–177 (2001) 458
Borges da Costa, J.A.T., see Javorsky, C.S. 175–177 (2001) 726
Borges, J.F.M., M.I. da Costa Jr, S.R. Teixeira, J.B.M. da Cunha and M.C.M. Alves, Solid-state reaction in Fe/V multilayers by ion beam mixing with thermal annealing 175–177 (2001) 485
Boudinov, H., J.P. de Souza and C. Jagadish, Electrical isolation of n-type InP by ion bombardment: Dose dependence and thermal stability 175–177 (2001) 235
Bouffard, S., see Benyagoub, A. 175–177 (2001) 417
Boxleitner, W., G. Hobler, V. Klüppel and H. Cerva, Simulation of topography evolution and damage formation during TEM sample preparation using focused ion beams 175–177 (2001) 102
Braithwaite, J.W., see Barbour, J.C. 175–177 (2001) 382
Brandt, R., see Sudowe, R. 175–177 (2001) 564
Brauer, G., see Fradin, J. 175–177 (2001) 516
Brebner, J.L., see Tchebotareva, A.L. 175–177 (2001) 187
Brebner, J.L., see Héliou, R. 175–177 (2001) 268
Breeger, B., see Wendler, E. 175–177 (2001) 78
Breeger, B., see Wendler, E. 175–177 (2001) 83
Breeger, B., see Stonert, A. 175–177 (2001) 219
Brett, D.A., see Jamieson, D.N. 175–177 (2001) 744
Burrows, C.P., see Gwilliam, R.M. 175–177 (2001) 62

Butler, T.M., see Lourenco, M.A. ... 175–177 (2001) 159
Byrne, A.P., see Glover, C.J. ... 175–177 (2001) 51

Cánepa, H.R., see Aguirre, M.H. ... 175–177 (2001) 274
Carosella, C.A., see Molnar, B. ... 175–177 (2001) 305
Carosella, C.A., see Schiestel, S. ... 175–177 (2001) 314
Carter, G., see Donnelly, S.E. ... 175–177 (2001) 132
Castañeda, S.I., V.A.A. Espinoza, F.L. Freire Jr, D.F. Franceschini and L.G. Jacobsohn, Surface modifications in diamond-like carbon films submitted to low-energy nitrogen ion bombardment ... 175–177 (2001) 699
Castro Vidaurre, E.F., C.A. Achete, R.A. Simão and A.C. Habert, Surface modification of porous polymeric membranes by RF-plasma treatment ... 175–177 (2001) 732
Castro, R.A., see Added, N. ... 175–177 (2001) 787
Cattaruzza, E., see Battaglin, G. ... 175–177 (2001) 410
Cerva, H., see Boxleitner, W. ... 175–177 (2001) 102
Chappert, C., see Devolder, T. ... 175–177 (2001) 375
Chayahara, A., see Heck, C. ... 175–177 (2001) 296
Chayahara, A., see Kinomura, A. ... 175–177 (2001) 319
Cheang-Wong, J.C., A. Oliver, J. Roiz, J.M. Hernández, L. Rodríguez-Fernández, J.G. Morales and A. Crespo-Sosa, Optical properties of Ir^{2+}-implanted silica glass ... 175–177 (2001) 490
Cheang-Wong, J.C., see Oliver, A. ... 175–177 (2001) 495
Chen, Y., see Devolder, T. ... 175–177 (2001) 375
Cheylan, S. and R.G. Elliman, Photoluminescence from Si nanocrystals in silica: The effect of hydrogen ... 175–177 (2001) 422
Cho, J.-S. and S.-K. Koh, Enhanced adhesion between polycarbonate substrates and tin-doped indium oxide films by ion-assisted reaction ... 175–177 (2001) 505
Cho, J.-S., see Kim, K.-H. ... 175–177 (2001) 542
Choi, D.-J., see Kim, K.-H. ... 175–177 (2001) 542
Chubaci, J.F.D., see Added, N. ... 175–177 (2001) 787
Clerc, C., see Ridgway, M.C. ... 175–177 (2001) 21
Coleman, P.G., see Gwilliam, R.M. ... 175–177 (2001) 62
Compagnini, G., G.G.N. Angilella, A. Raudino and O. Puglisi, Memory effect on ion beam-induced depolymerization of PMMA ... 175–177 (2001) 559
Couvreur, F., see Benyagoub, A. ... 175–177 (2001) 417
Crespo-Sosa, A., see Cheang-Wong, J.C. ... 175–177 (2001) 490
Crespos, A., see Oliver, A. ... 175–177 (2001) 495
Cruz, M.M., see Marques, C. ... 175–177 (2001) 500
Cuscó, R., see Ibáñez, J. ... 175–177 (2001) 246
Cuscó, R., see Marcos, B. ... 175–177 (2001) 252

D'Acapito, F., see Battaglin, G. ... 175–177 (2001) 410
D'Acapito, F., see de Julián Fernández, C. ... 175–177 (2001) 479
da Costa Jr, M.I., see Borges, J.F.M. ... 175–177 (2001) 485
da Cruz, N.C., see Rangel, E.C. ... 175–177 (2001) 594
da Cruz, N.C., E.C. Rangel, M.H. Tabacniks, B.C. Trasferetti and C.U. Davanzo, The effect of ion bombardment on the properties of TiO_x films deposited by a modified ion-assisted PECVD technique ... 175–177 (2001) 721
da Cunha, J.B.M., see Borges, J.F.M. ... 175–177 (2001) 485
da Jornada, J.A.H., see Soares, S.R.S. ... 175–177 (2001) 474
da Rosa, E.B.O., S. Gonçalves, R.M.C. de Almeida, I.J.R. Baumvol and F.C. Stedile, Ion beams as analytical tools in the thermal growth of ultrathin silicon oxide films ... 175–177 (2001) 762
da Silva, D.L., G. de M. Azevedo, M. Behar, J.F. Dias and P.L. Grande, Random energy loss and straggling study of Li into Si ... 175–177 (2001) 98
da Silva, D.L., P.F.P. Fichtner, A. Peeva, M. Behar, R. Koegler and W. Skorupa, The effects of implantation temperature on He bubble formation in silicon ... 175–177 (2001) 335
da Silva, M.D., see Beloto, A.F. ... 175–177 (2001) 224
da Silva, M.F., see Alves, E. ... 175–177 (2001) 241
da Silva, M.F., see Kling, A. ... 175–177 (2001) 331
da Silva, M.F., see Kling, A. ... 175–177 (2001) 394
da Silva, R.C., see Marques, C. ... 175–177 (2001) 500

Danilov, I., L.L. Pataro, M.P.P. de Castro, G.C. do Nascimento and N.C. Frateschi, Electrical and optical effects of He^+ ion irradiation in InGaP/GaAs/InGaAs lasers ... 175–177 (2001) 782
Daulton, T.L., M.A. Kirk, R.S. Lewis and L.E. Rehn, Production of nanodiamonds by high-energy ion irradiation of graphite at room temperature ... 175–177 (2001) 12
Davanzo, C.U., see da Cruz, N.C. ... 175–177 (2001) 721
de Almeida, R.M.C., see da Rosa, E.B.O. ... 175–177 (2001) 762
de Castro, M.P.P., see Danilov, I. ... 175–177 (2001) 782
de Julian Fernandez, C., see Battaglin, G. ... 175–177 (2001) 410
de Julián Fernández, C., C. Sangregorio, G. Mattei, C. Maurizio, G. Battaglin, F. Gonella, A. Lascialfari, S. Lo Russo, D. Gatteschi, P. Mazzoldi, J.M. Gonzalez and F. D'Acapito, Magnetic properties of Co and Ni based alloy nanoparticles dispersed in a silica matrix ... 175–177 (2001) 479
de la Puente, E., see Ibáñez, J. ... 175–177 (2001) 246
De Marchi, G., see Battaglin, G. ... 175–177 (2001) 410
de Souza, J.P., M. Behar, J.F. Dias and J.H.R. dos Santos, Range parameters of ^{18}O implanted into Si and SiO_2 ... 175–177 (2001) 46
de Souza, J.P., see Boudinov, H. ... 175–177 (2001) 235
Desnica-Frankovic, I.D., see Ridgway, M.C. ... 175–177 (2001) 21
Devolder, T., H. Bernas, D. Ravelosona, C. Chappert, S. Pizzini, J. Vogel, J. Ferré, J.-P. Jamet, Y. Chen and V. Mathet, Beam-induced magnetic property modifications: Basics, nanostructure fabrication and potential applications ... 175–177 (2001) 375
Dharmarasu, N., see Wesch, W. ... 175–177 (2001) 257
Dias, J.F., see de Souza, J.P. ... 175–177 (2001) 46
Dias, J.F., see da Silva, D.L. ... 175–177 (2001) 98
DiGregorio, D.E., see Huck, H. ... 175–177 (2001) 772
do Nascimento, G.C., see Danilov, I. ... 175–177 (2001) 782
Doi, Y., see Kobayashi, T. ... 175–177 (2001) 548
Donnelly, S.E., see Birtcher, R.C. ... 175–177 (2001) 40
Donnelly, S.E., V.M. Vishnyakov, R.C. Birtcher and G. Carter, The effects of radiation damage and impurities on void dynamics in silicon ... 175–177 (2001) 132
dos Santos, J.H.R., see de Souza, J.P. ... 175–177 (2001) 46
Dowd, A., D. Llewellyn, R.G. Elliman, B. Luther-Davies, M. Samoc and J.D. Fitz Gerald, Physical and optical characterisation of Ge-implanted silica ... 175–177 (2001) 637
Dufour, C., see Benyagoub, A. ... 175–177 (2001) 417
Dufour, Ch., see Boccanfuso, M. ... 175–177 (2001) 590
Dupasquier, A., see Puglisi, O. ... 175–177 (2001) 605

Ebisu, H., see Nakashima, K. ... 175–177 (2001) 208
Eckardt, J.C. and G.H. Lantschner, Experimental energy straggling of protons in thin solid foils ... 175–177 (2001) 93
Ecker, K.H., A. Berger, R. Grötzschel, L. Persson and U. Wätjen, Antimony implanted in silicon – A thin layer reference material for surface analysis ... 175–177 (2001) 797
Elliman, R.G., see Stritzker, B. ... 175–177 (2001) 193
Elliman, R.G., see Cheylan, S. ... 175–177 (2001) 422
Elliman, R.G., see Dowd, A. ... 175–177 (2001) 637
Enders, B., see Lensch, O. ... 175–177 (2001) 683
Ensinger, W., see Sudowe, R. ... 175–177 (2001) 564
Ensinger, W., see Volz, K. ... 175–177 (2001) 569
Ensinger, W., see Lensch, O. ... 175–177 (2001) 575
Ensinger, W., see Galonska, M. ... 175–177 (2001) 658
Ensinger, W., see Lensch, O. ... 175–177 (2001) 683
Eriguchi, E., see Taniguchi, S. ... 175–177 (2001) 647
Eryu, O., see Nakashima, K. ... 175–177 (2001) 208
Espinoza, V.A.A., see Castañeda, S.I. ... 175–177 (2001) 699
Ewing, R.C., see Wang, S.X. ... 175–177 (2001) 615

Fatemi, M., see Molnar, B. ... 175–177 (2001) 305
Feldmann, G., P.F.P. Fichtner and F.C. Zawislak, Nucleation and growth behavior of Cu–Al precipitates in He implanted and annealed aluminum ... 175–177 (2001) 432

Fernández Niello, J.O., see Huck, H. ... 175–177 (2001) 772
Ferré, J., see Devolder, T. ... 175–177 (2001) 375
Fichtner, P.F.P., see Peeva, A. ... 175–177 (2001) 176
Fichtner, P.F.P., see Kling, A. ... 175–177 (2001) 331
Fichtner, P.F.P., see da Silva, D.L. ... 175–177 (2001) 335
Fichtner, P.F.P., see Holländer, B. ... 175–177 (2001) 357
Fichtner, P.F.P., see Kling, A. ... 175–177 (2001) 394
Fichtner, P.F.P., see Feldmann, G. ... 175–177 (2001) 432
Fink, D., see Hnatowicz, V. ... 175–177 (2001) 437
Fitz Gerald, J.D., see Dowd, A. ... 175–177 (2001) 637
Foerster, C.E., C.M. Lepienski, F.C. Nascimento and F.C. Serbena, The effects of Ar post-bombardment and heat treatment on hardness of N implanted iron ... 175–177 (2001) 511
Foerster, C.E., see Lepienski, C.M. ... 175–177 (2001) 668
Foerster, C.E., see Lopes, J.M.J. ... 175–177 (2001) 673
Földvári, I., see Kling, A. ... 175–177 (2001) 331
Foran, G.J., see Ridgway, M.C. ... 175–177 (2001) 21
Foran, G.J., see Ridgway, M.C. ... 175–177 (2001) 280
Fradin, J., T. Thomé, R.I. Grynszpan, L. Thomé, W. Anwand and G. Brauer, Precursory stage of damage production in argon irradiated cubic zirconia ... 175–177 (2001) 516
Fragalà, M.E., see Puglisi, O. ... 175–177 (2001) 605
Franceschini, D.F., see Castañeda, S.I. ... 175–177 (2001) 699
Franzò, G., E.C. Moreira, D. Pacifici, F. Priolo, F. Iacona and C. Spinella, Ion beam synthesis of undoped and Er-doped Si nanocrystals ... 175–177 (2001) 140
Frateschi, N.C., see Danilov, I. ... 175–177 (2001) 782
Freire Jr, F.L., see Jacobsohn, L.G. ... 175–177 (2001) 442
Freire Jr, F.L., see Castañeda, S.I. ... 175–177 (2001) 699
Friedland, E., see Auret, F.D. ... 175–177 (2001) 292
Fukarek, W., see van Dillen, T. ... 175–177 (2001) 350
Furic, K., see Ridgway, M.C. ... 175–177 (2001) 21
Furuya, K., see Mitsuishi, K. ... 175–177 (2001) 74

Gabor, Ch., see Galonska, M. ... 175–177 (2001) 658
Galonska, M., Ch. Gabor, R.W. Thomae, H. Klein, K. Volz and W. Ensinger, Determination of ion incidence angles in plasma immersion ion implantation by means of a hollow multi-aperture target ... 175–177 (2001) 658
Gamo, K., see Hada, T. ... 175–177 (2001) 751
Garcia, I.T.S., see Lepienski, C.M. ... 175–177 (2001) 668
Garrido, F., see Thomé, L. ... 175–177 (2001) 453
Gärtner, K., see Weber, B. ... 175–177 (2001) 119
Gatteschi, D., see de Julián Fernández, C. ... 175–177 (2001) 479
Gentils, A., see Thomé, L. ... 175–177 (2001) 453
Gibart, P., see Auret, F.D. ... 175–177 (2001) 292
Glover, C.J., see Ridgway, M.C. ... 175–177 (2001) 21
Glover, C.J., A.P. Byrne and M.C. Ridgway, Irradiation-induced defect configurations in Ge substrates characterised with perturbed angular correlation ... 175–177 (2001) 51
Glover, C.J., see Ridgway, M.C. ... 175–177 (2001) 280
Gonçalves, S., see da Rosa, E.B.O. ... 175–177 (2001) 762
Gonella, F., see Battaglin, G. ... 175–177 (2001) 410
Gonella, F., see de Julián Fernández, C. ... 175–177 (2001) 479
Gonzalez, J.M., see de Julián Fernández, C. ... 175–177 (2001) 479
González-Díaz, G., see Marcos, B. ... 175–177 (2001) 252
Goodman, S., see Vantomme, A. ... 175–177 (2001) 148
Goodman, S.A., see Auret, F.D. ... 175–177 (2001) 292
Gösele, U., see Kögler, R. ... 175–177 (2001) 340
Gossmann, H.-J., see Kalyanaraman, R. ... 175–177 (2001) 182
Graczyk, M., see Zhang, Y. ... 175–177 (2001) 737
Grande, P.L., see Schiwietz, G. ... 175–177 (2001) 1
Grande, P.L., see da Silva, D.L. ... 175–177 (2001) 98

Grande, P.L., see Schiwietz, G. ... 175–177 (2001) 125
Gritsyna, V.T., see Takeda, Y. ... 175–177 (2001) 463
Gritsyna, V.T., see Okubo, N. ... 175–177 (2001) 663
Grötzschel, R., see Jagielski, J. ... 175–177 (2001) 448
Grözschel, R., see Werner, Z. ... 175–177 (2001) 767
Grötzschel, R., see Ecker, K.H. ... 175–177 (2001) 797
Grynszpan, R.I., see Fradin, J. ... 175–177 (2001) 516
Gujrathi, S.C., see Qian, C. ... 175–177 (2001) 711
Günzel, R., see Abramof, E. ... 175–177 (2001) 229
Gunzel, R., see Ueda, M. ... 175–177 (2001) 715
Guzman, L., see Wolf, G.K. ... 175–177 (2001) 756
Gwilliam, R.M., A.P. Knights, A. Nejim, B.J. Sealy, C.P. Burrows, F. Malik and P.G. Coleman, The study of lattice damage using slow positrons following low energy B^+ implantation of silicon ... 175–177 (2001) 62
Gwilliam, R.M., see Lourenco, M.A. ... 175–177 (2001) 159
Gwilliam, R.M., see Lourenco, M.A. ... 175–177 (2001) 300
Gwilliam, R.M., see Milosavljevic, M. ... 175–177 (2001) 309

Habert, A.C., see Castro Vidaurre, E.F. ... 175–177 (2001) 732
Hackbarth, T., see Holländer, B. ... 175–177 (2001) 357
Hada, T., H. Miyamoto, J. Yanagisawa, F. Wakaya, Y. Yuba and K. Gamo, Carrier activation in in situ Si-doped GaAs layers fabricated by a focused Si ion beam and molecular beam epitaxy combined system ... 175–177 (2001) 751
Halac, E.B., see Huck, H. ... 175–177 (2001) 772
Hansen, J.L., see Ridgway, M.C. ... 175–177 (2001) 21
Hayes, M., see Auret, F.D. ... 175–177 (2001) 292
Haynes, T.E., see Kalyanaraman, R. ... 175–177 (2001) 182
He, X.M., see Peters, A.M. ... 175–177 (2001) 599
Heck, C., A. Chayahara, Y. Horino, Y. Yokota, R.M. Miranda, A.B. Antunes, M.M. Miranda and M.N. Baibich, Electronic transport in thin Cr films modified by Fe ion implantation ... 175–177 (2001) 296
Heck, C., see Kinomura, A. ... 175–177 (2001) 319
Heinig, K.-H., see Müller, T. ... 175–177 (2001) 468
Heitz, J., see Hnatowicz, V. ... 175–177 (2001) 437
Héliou, R., J.L. Brebner and S. Roorda, Optical and structural properties of 6H–SiC implanted with silicon as a function of implantation dose and temperature ... 175–177 (2001) 268
Hernández, J.M., see Cheang-Wong, J.C. ... 175–177 (2001) 490
Hernández, J.M., see Oliver, A. ... 175–177 (2001) 495
Herzog, H.-J., see Holländer, B. ... 175–177 (2001) 357
Heuer, J.K., see Lam, N.Q. ... 175–177 (2001) 388
Heyden, D., D. Müller, G.K. Wolf, L. Amaral and M. Behar, Modification of stainless steel and aluminium with pulsed energetic ion beams in the millisecond regime ... 175–177 (2001) 403
Hnatowicz, V., V. Peřina, A. Macková, V. Švorčík, V. Rybka, D. Fink and J. Heitz, Degradation of polyimide by 100 keV He^+, Ne^+, Ar^+ and Kr^+ ions ... 175–177 (2001) 437
Hobler, G., see Boxleitner, W. ... 175–177 (2001) 102
Höchbauer, T., A. Misra, R. Verda, Y. Zheng, S.S. Lau, J.W. Mayer and M. Nastasi, The influence of ion-implantation damage on hydrogen-induced ion-cut ... 175–177 (2001) 169
Höche, Th., see Wesch, W. ... 175–177 (2001) 88
Hogg, S.M., see Vantomme, A. ... 175–177 (2001) 148
Hogg, S.M., A. Vantomme, M.F. Wu, B. Pipeleers and M. Swart, Temperature and angular effects on the channelled implantation of Er into Si⟨1 1 1⟩ ... 175–177 (2001) 585
Holländer, B., St. Lenk, S. Mantl, H. Trinkaus, D. Kirch, M. Luysberg, T. Hackbarth, H.-J. Herzog and P.F.P. Fichtner, Strain relaxation of pseudomorphic $Si_{1-x}Ge_x$/Si(1 0 0) heterostructures after hydrogen or helium ion implantation for virtual substrate fabrication ... 175–177 (2001) 357
Hollar, E.P., see Jenčič, I. ... 175–177 (2001) 197
Homewood, K.P., see Lourenco, M.A. ... 175–177 (2001) 159
Homewood, K.P., see Lourenco, M.A. ... 175–177 (2001) 300
Homewood, K.P., see Milosavljevic, M. ... 175–177 (2001) 309
Horino, Y., see Heck, C. ... 175–177 (2001) 296

Horino, Y., see Kinomura, A. ... 175–177 (2001) 319
Hubler, G.K., see Schiestel, S. ... 175–177 (2001) 314
Hübler, R., see Blando, E. ... 175–177 (2001) 620
Hübler, R., see Tentardini, E.K. ... 175–177 (2001) 626
Hübler, R., Ion beam mixing of Ti–TiN multilayers for tribological and corrosion protection ... 175–177 (2001) 630
Huck, H., D.E. DiGregorio, J.O. Fernández Niello, E.B. Halac, M. Igarzábal, J. Orecchia and M.E. Reinoso, New compact design for an ion source ... 175–177 (2001) 772
Hullavarad, S.S., see Auret, F.D. ... 175–177 (2001) 292

Iacona, F., see Franzò, G. ... 175–177 (2001) 140
Iakoubovskii, K., see Vantomme, A. ... 175–177 (2001) 148
Ibáñez, J., R. Cuscó, L. Artús, E. de la Puente and J. Jiménez, Evaluation of free-carrier concentration in Si^+-implanted InP by means of photoluminescence ... 175–177 (2001) 246
Ibáñez, J., see Marcos, B. ... 175–177 (2001) 252
Igarzábal, M., see Huck, H. ... 175–177 (2001) 772
Ikeyama, M., see Nakao, S. ... 175–177 (2001) 202
Ikeyama, M., S. Nakao, M. Tazawa, K. Kadono and K. Kamada, Optical property changes of silica glass and sapphire induced by Cu and O implantation ... 175–177 (2001) 652
Ishida, T., see Kimura, T. ... 175–177 (2001) 286
Ishikawa, H., see Nakano, S. ... 175–177 (2001) 777
Isshiki, H., see Kimura, T. ... 175–177 (2001) 286
Iwaki, M., Ion surface treatments on organic materials ... 175–177 (2001) 368
Iwaki, M., see Toida, H. ... 175–177 (2001) 532
Iwaki, M., see Kobayashi, T. ... 175–177 (2001) 548
Iwaki, M., see Aono, K. ... 175–177 (2001) 580
Iwaki, M., see Kurotobi, K. ... 175–177 (2001) 791
Iwase, A., see Matsunami, N. ... 175–177 (2001) 56
Iwata, T., see Kobayashi, T. ... 175–177 (2001) 548

Jacobs, K., see Vantomme, A. ... 175–177 (2001) 148
Jacobsohn, L.G. and F.L. Freire Jr, Germanium implantation into amorphous carbon films ... 175–177 (2001) 442
Jacobsohn, L.G., see Castañeda, S.I. ... 175–177 (2001) 699
Jacobson, D.C., see Kalyanaraman, R. ... 175–177 (2001) 182
Jagadish, C., see Kucheyev, S.O. ... 175–177 (2001) 214
Jagadish, C., see Boudinov, H. ... 175–177 (2001) 235
Jagielski, J., M. Kopcewicz, W. Matz, R. Grötzschel and L. Thomé, Phase transformations in nitrogen-implanted iron layers ... 175–177 (2001) 448
Jagielski, J., see Thomé, L. ... 175–177 (2001) 453
Jamet, J.-P., see Devolder, T. ... 175–177 (2001) 375
Jamieson, D.N., see Orwa, J.O. ... 175–177 (2001) 554
Jamieson, D.N., S. Prawer, I. Andrienko, D.A. Brett and V. Millar, A role for ion implantation in quantum computing ... 175–177 (2001) 744
Javorsky, C.S., T.R. Strohaecker, J.A.T. Borges da Costa and M.A.Z. Vasconcellos, Ion beam analysis of plasma nitrided Ti6Al4V-ELI ... 175–177 (2001) 726
Jenčič, I., E.P. Hollar and I.M. Robertson, Electron-induced regrowth of isolated amorphous zones in GaAs 175–177 (2001) 197
Jeynes, C., see Milosavljevic, M. ... 175–177 (2001) 309
Jiang, W., see Weber, W.J. ... 175–177 (2001) 26
Jiang, W., W.J. Weber and S. Thevuthasan, Damage accumulation and recovery in gold-ion-irradiated barium titanate ... 175–177 (2001) 610
Jiménez, J., see Ibáñez, J. ... 175–177 (2001) 246

Kögler, R., A. Peeva, P. Werner, W. Skorupa and U. Gösele, Gettering centres in high-energy ion-implanted silicon investigated by point defect recombination ... 175–177 (2001) 340
Kadono, K., see Ikeyama, M. ... 175–177 (2001) 652
Kaibara, M., see Kurotobi, K. ... 175–177 (2001) 791
Kalyanaraman, R., T.E. Haynes, M. Yoon, B.C. Larson, D.C. Jacobson, H.-J. Gossmann and C.S. Rafferty, Quantitative evolution of vacancy-type defects in high-energy ion-implanted Si: Au labeling and the vacancy implanter ... 175–177 (2001) 182

Kamada, K., see Ikeyama, M. ... 175–177 (2001) 652
Keinonen, J., see Nordlund, K. ... 175–177 (2001) 31
Kench, P.J., J.M. Shannon, G. Shao, P. Tsakiropoulos and S.R.P. Silva, Ion beam synthesis of gallium nitride ... 175–177 (2001) 678
Kewell, A.K., see Lourenco, M.A. ... 175–177 (2001) 159
Kim, K.-H., J.-S. Cho, D.-J. Choi and S.-K. Koh, Hydrophilic group formation and cell culturing on polystyrene Petri-dish modified by ion-assisted reaction ... 175–177 (2001) 542
Kimura, T., H. Toda, T. Ishida, H. Isshiki and R. Saito, Study of the radiative and nonradiative processes of rare earth implanted semiconductors at low temperatures ... 175–177 (2001) 286
Kinomura, A., A. Chayahara, N. Tsubouchi, C. Heck, Y. Horino and Y. Miyagawa, Movement of defects and atoms during ion beam induced crystallization ... 175–177 (2001) 319
Kirch, D., see Holländer, B. ... 175–177 (2001) 357
Kirk, M.A., see Daulton, T.L. ... 175–177 (2001) 12
Kirkby, K.J., see Lourenco, M.A. ... 175–177 (2001) 159
Kishimoto, N., see Bandourko, V. ... 175–177 (2001) 68
Kishimoto, N., see Amekura, H. ... 175–177 (2001) 345
Kishimoto, N., N. Okubo, C.G. Lee, N. Umeda and Y. Takeda, Co-irradiation effects of intense heavy ions and photons on surface modification of insulators ... 175–177 (2001) 426
Kishimoto, N., see Takeda, Y. ... 175–177 (2001) 463
Kishimoto, N., see Okubo, N. ... 175–177 (2001) 663
Kitahara, A., see Taniguchi, S. ... 175–177 (2001) 647
Kiuchi, M., see Lensch, O. ... 175–177 (2001) 575
Klatt, Ch., see Volz, K. ... 175–177 (2001) 569
Klein, H., see Galonska, M. ... 175–177 (2001) 658
Kling, A., M.F. da Silva, J.C. Soares, P.F.P. Fichtner, L. Amaral, F. Zawislak, I. Földvári and Á. Péter, Formation of nanoclusters in Au-implanted bismuth tellurite ... 175–177 (2001) 331
Kling, A., M.F. da Silva, J.C. Soares, P.F.P. Fichtner, L. Amaral and F. Zawislak, Defect evolution and characterization in He-implanted $LiNbO_3$ ... 175–177 (2001) 394
Klüppel, V., see Boxleitner, W. ... 175–177 (2001) 102
Knecht, J., see Lensch, O. ... 175–177 (2001) 683
Knies, D., see Schiestel, S. ... 175–177 (2001) 314
Knights, A.P., see Gwilliam, R.M. ... 175–177 (2001) 62
Knights, A.P., see Lourenco, M.A. ... 175–177 (2001) 300
Kobayashi, T., see Toida, H. ... 175–177 (2001) 532
Kobayashi, T., T. Iwata, Y. Doi and M. Iwaki, Metallic nanoparticles formed in polyimide by ion implantation ... 175–177 (2001) 548
Koegler, R., see Peeva, A. ... 175–177 (2001) 176
Koegler, R., see da Silva, D.L. ... 175–177 (2001) 335
Koh, S.-K., see Cho, J.-S. ... 175–177 (2001) 505
Koh, S.-K., see Kim, K.-H. ... 175–177 (2001) 542
Kopcewicz, M., see Jagielski, J. ... 175–177 (2001) 448
Krug, C., T.D.M. Salgado, F.C. Stedile and I.J.R. Baumvol, Low energy nitrogen implantation into Si and SiO_2/Si ... 175–177 (2001) 694
Krug, C., C. Radtke, F.C. Stedile and I.J.R. Baumvol, Isotope-beam modification of materials at eV energies ... 175–177 (2001) 705
Kucheyev, S.O., J.S. Williams, J. Zou, C. Jagadish and G. Li, High-dose ion implantation into GaN ... 175–177 (2001) 214
Kurotobi, K., M. Kaibara, Y. Suzuki, M. Iwaki and H. Nakajima, Plasma protein adsorption onto cell attachment controlled ion implanted collagen ... 175–177 (2001) 791

Lam, N.Q., P.R. Okamoto and J.K. Heuer, Applications of disorder-induced melting concept to critical-solute-accumulation processes ... 175–177 (2001) 388
Lam, N.Q., see Moura, C.S. ... 175–177 (2001) 526
Langouche, G., see Wahl, U. ... 175–177 (2001) 262
Lantschner, G.H., see Eckardt, J.C. ... 175–177 (2001) 93
Larson, B.C., see Kalyanaraman, R. ... 175–177 (2001) 182
Lascialfari, A., see de Julián Fernández, C. ... 175–177 (2001) 479
Lau, S.S., see Höchbauer, T. ... 175–177 (2001) 169
Lay, T.T., see Bandourko, V. ... 175–177 (2001) 68
Lee, C.G., see Bandourko, V. ... 175–177 (2001) 68
Lee, C.G., see Amekura, H. ... 175–177 (2001) 345

Lee, C.G., see Kishimoto, N. ... 175–177 (2001) 426
Lee, T.W., see Ridgway, M.C. ... 175–177 (2001) 280
Legodi, M.J., see Auret, F.D. ... 175–177 (2001) 292
Leite, N.F., see Beloto, A.F. ... 175–177 (2001) 224
Lenk, St., see Holländer, B. ... 175–177 (2001) 357
Lensch, O., K. Volz, M. Kiuchi and W. Ensinger, Pitting corrosion of aluminium coated with amorphous carbon films by argon ion beam assisted deposition at low process temperature ... 175–177 (2001) 575
Lensch, O., B. Enders, J. Knecht and W. Ensinger, Examination of the metastable and stable pitting corrosion of aluminum modified with carbon by ion beam techniques ... 175–177 (2001) 683
Lepienski, C.M., I.T.S. Garcia, C.E. Foerster, F.C. Serbena and F.C. Zawislak, Mechanical properties of He irradiated and annealed AZ-1350 J^{TM} films ... 175–177 (2001) 668
Lepienski, C.M., see Foerster, C.E. ... 175–177 (2001) 511
Lepienski, C.M., see Rangel, E.C. ... 175–177 (2001) 594
Lepienski, C.M., see Lopes, J.M.J. ... 175–177 (2001) 673
Levesque, F., see Benyagoub, A. ... 175–177 (2001) 417
Lewis, R.S., see Daulton, T.L. ... 175–177 (2001) 12
Li, G., see Kucheyev, S.O. ... 175–177 (2001) 214
Liguori Neto, R., see Added, N. ... 175–177 (2001) 787
Lindner, J.K.N., S. Wenzel and B. Stritzker, Metallization of ion beam synthesized Si/3C–SiC/Si layer systems by high-dose implantation of transition metal ions ... 175–177 (2001) 324
Liu, A.C.Y., J.C. McCallum and J. Wong-Leung, The crystallisation of deep amorphous wells in silicon produced by ion implantation ... 175–177 (2001) 164
Liu, C., see Alves, E. ... 175–177 (2001) 241
Livi, R.P., see Soares, S.R.S. ... 175–177 (2001) 474
Llewellyn, D., see Dowd, A. ... 175–177 (2001) 637
Lo Russo, S., see de Julián Fernández, C. ... 175–177 (2001) 479
Lopes, J.M.J., C.E. Foerster, F.C. Serbena, C.M. Lepienski, D.L. Baptista and F.C. Zawislak, Nanoscratch testing of C_{60} thin films irradiated with N ions ... 175–177 (2001) 673
Lourenco, M.A., T.M. Butler, A.K. Kewell, R.M. Gwilliam, K.J. Kirkby and K.P. Homewood, Electrical, electronic and optical characterisation of ion beam synthesised β-$FeSi_2$ light emitting devices ... 175–177 (2001) 159
Lourenco, M.A., A.P. Knights, K.P. Homewood, R.M. Gwilliam, P.J. Simpson and P. Mascher, A comparative study of vacancies produced by proton implantation of silicon using positron annihilation and deep level transient spectroscopy ... 175–177 (2001) 300
Lu, D.-T., see Zhang, Y. ... 175–177 (2001) 737
Luderer, E., see Schiwietz, G. ... 175–177 (2001) 1
Luther-Davies, B., see Dowd, A. ... 175–177 (2001) 637
Luysberg, M., see Holländer, B. ... 175–177 (2001) 357
Lynn, K.G., see Puglisi, O. ... 175–177 (2001) 605

Macková, A., see Hnatowicz, V. ... 175–177 (2001) 437
Maeda, Y., see Nakashima, K. ... 175–177 (2001) 208
Malik, F., see Gwilliam, R.M. ... 175–177 (2001) 62
Mansano, R.D., see Added, N. ... 175–177 (2001) 787
Mantl, S., see Holländer, B. ... 175–177 (2001) 357
Marcos, B., J. Ibáñez, R. Cuscó, F.L. Martínez, G. González-Díaz and L. Artús, Lattice recovery by rapid thermal annealing in Mg^+-implanted InP assessed by Raman spectroscopy ... 175–177 (2001) 252
Marques, C., M.M. Cruz, R.C. da Silva and E. Alves, Study of new surface structures created on sapphire by Co ion implantation ... 175–177 (2001) 500
Martínez, F.L., see Marcos, B. ... 175–177 (2001) 252
Mascher, P., see Lourenco, M.A. ... 175–177 (2001) 300
Mathet, V., see Devolder, T. ... 175–177 (2001) 375
Matsunami, N., M. Sataka and A. Iwase, Sputtering of high T_c superconductor $YBa_2Cu_3O_{7-\delta}$ by high energy heavy ions ... 175–177 (2001) 56
Matsuo, J., see Birtcher, R.C. ... 175–177 (2001) 36
Matsuoka, M., see Added, N. ... 175–177 (2001) 787
Mattei, G., see Battaglin, G. ... 175–177 (2001) 410
Mattei, G., see de Julián Fernández, C. ... 175–177 (2001) 479

Matz, W., see Jagielski, J. ... 175–177 (2001) 448
Maurizio, C., see Battaglin, G. ... 175–177 (2001) 410
Maurizio, C., see de Julián Fernández, C. ... 175–177 (2001) 479
Maximov, I.A., see Zhang, Y. ... 175–177 (2001) 737
Mayer, J.W., see Höchbauer, T. ... 175–177 (2001) 169
Mazzoldi, P., see Battaglin, G. ... 175–177 (2001) 410
Mazzoldi, P., see de Julián Fernández, C. ... 175–177 (2001) 479
McCallum, J.C., see Liu, A.C.Y. ... 175–177 (2001) 164
McCallum, J.C., see Morpeth, L.D. ... 175–177 (2001) 537
McCallum, J.C., see Orwa, J.O. ... 175–177 (2001) 554
McKinty, C.N., see Milosavljevic, M. ... 175–177 (2001) 309
Millar, V., see Jamieson, D.N. ... 175–177 (2001) 744
Milosavljevic, M., G. Shao, R.M. Gwilliam, C. Jeynes, C.N. McKinty and K.P. Homewood, Properties of β-$FeSi_2$ grown by combined ion irradiation and annealing of Fe/Si bilayers ... 175–177 (2001) 309
Miotello, A., see Battaglin, G. ... 175–177 (2001) 410
Miranda, M.M., see Heck, C. ... 175–177 (2001) 296
Miranda, R.M., see Heck, C. ... 175–177 (2001) 296
Misra, A., see Höchbauer, T. ... 175–177 (2001) 169
Misra, A. and M. Nastasi, Intrinsic residual stresses in metal films synthesized by energetic particle deposition ... 175–177 (2001) 688
Mitsuishi, K., M. Song, H. Yasuda and K. Furuya, Effect of Ar irradiation to Xe precipitate in Al ... 175–177 (2001) 74
Miyagawa, S., see Nakao, S. ... 175–177 (2001) 202
Miyagawa, Y., see Nakao, S. ... 175–177 (2001) 202
Miyagawa, Y., see Kinomura, A. ... 175–177 (2001) 319
Miyamoto, H., see Hada, T. ... 175–177 (2001) 751
Moerman, I., see Vantomme, A. ... 175–177 (2001) 148
Molnar, B., M. Fatemi, S.B. Qadri and C.A. Carosella, Correlation between the depth profiles of the implantation-induced carriers and the lattice strains in high-energy implanted and annealed InP ... 175–177 (2001) 305
Moon, Y., see Ridgway, M.C. ... 175–177 (2001) 280
Morales, J.G., see Cheang-Wong, J.C. ... 175–177 (2001) 490
Moreira, E.C., see Franzò, G. ... 175–177 (2001) 140
Morpeth, L.D. and J.C. McCallum, Ti:sapphire formation via the co-implantation of Ti and O ions into sapphire ... 175–177 (2001) 537
Motta, A.T., A. Paesano Jr, R.C. Birtcher and L. Amaral, Grain growth in Zr–Fe multilayers under in situ ion irradiation ... 175–177 (2001) 521
Motta, A.T., see Moura, C.S. ... 175–177 (2001) 526
Moura, C.S., A.T. Motta, N.Q. Lam and L. Amaral, Point defect energetics in the ZrNi and Zr_2Ni intermetallics ... 175–177 (2001) 526
Mozolevski, I.E., High energy ion range and deposited energy calculation using the Boltzmann–Fokker–Planck splitting of the Boltzmann transport equation ... 175–177 (2001) 113
Müller, D., see Heyden, D. ... 175–177 (2001) 403
Müller, T., K.-H. Heinig and B. Schmidt, Formation of Ge nanowires in oxidized silicon V-grooves by ion beam synthesis ... 175–177 (2001) 468
Münz, R., see Wolf, G.K. ... 175–177 (2001) 756

Nagel, R. and A.G. Balogh, On the behaviour of enhanced mixing in metal/ceramic interfaces ... 175–177 (2001) 398
Nakagawa, S., see Nakano, S. ... 175–177 (2001) 777
Nakajima, H., see Kurotobi, K. ... 175–177 (2001) 791
Nakano, S., see Ogiso, H. ... 175–177 (2001) 641
Nakano, S., S. Nakagawa, H. Ishikawa and H. Ogiso, Fabrication of micromechanical structures on substrates selectively etched using a micropatterned ion-implantation method ... 175–177 (2001) 777
Nakao, S., S.X. Wang, L.M. Wang, M. Ikeyama, Y. Miyagawa and S. Miyagawa, Microstructure of high-energy O and Cu ion-implanted silica glasses ... 175–177 (2001) 202
Nakao, S., see Ikeyama, M. ... 175–177 (2001) 652
Nakashima, K., O. Eryu, H. Akiyama, Y. Maeda and H. Ebisu, Correlation between Er-luminescent centers and defects in Si co-implanted with Er and O ... 175–177 (2001) 208
Nascimento, F.C., see Foerster, C.E. ... 175–177 (2001) 511
Nastasi, M., see Höchbauer, T. ... 175–177 (2001) 169

Nastasi, M., see Peters, A.M. 175–177 (2001) 599
Nastasi, M., see Misra, A. 175–177 (2001) 688
Nejim, A., see Gwilliam, R.M. 175–177 (2001) 62
Nord, J., see Nordlund, K. 175–177 (2001) 31
Nordlund, K., J. Nord and J. Keinonen, Chemical effects in collision cascades 175–177 (2001) 31
Nowicki, L., see Stonert, A. 175–177 (2001) 219
Nylandsted Larsen, A., see Ridgway, M.C. 175–177 (2001) 21

Ogiso, H., S. Nakano, H. Tokumoto and K. Yamanaka, Nano-scale elastic property changes of ion-implanted graphite 175–177 (2001) 641
Ogiso, H., see Nakano, S. 175–177 (2001) 777
Okamoto, P.R., see Lam, N.Q. 175–177 (2001) 388
Okubo, N., see Amekura, H. 175–177 (2001) 345
Okubo, N., see Kishimoto, N. 175–177 (2001) 426
Okubo, N., Y. Takeda, H. Amekura, J.P. Zhao, V.T. Gritsyna and N. Kishimoto, Surface smoothening and compaction of silica glass under dynamic negative ion mixing 175–177 (2001) 663
Oliver, A., see Cheang-Wong, J.C. 175–177 (2001) 490
Oliver, A., J.C. Cheang-Wong, J. Roiz, J.M. Hernández, L. Rodríguez-Fernández and A. Crespos, Optical absorption and emission studies of 2 MeV Cu-implanted silica glass 175–177 (2001) 495
Opfermann, Th., see Wesch, W. 175–177 (2001) 88
Orecchia, J., see Huck, H. 175–177 (2001) 772
Orwa, J.O., D.N. Jamieson, S. Prawer and J.C. McCallum, Carbon diffusion and nanocrystalline diamond formation in carbon ion-implanted oxides studied by nuclear elastic scattering 175–177 (2001) 554
Osada, M., see Toida, H. 175–177 (2001) 532

Pacifici, D., see Franzò, G. 175–177 (2001) 140
Paesano Jr, A., see Motta, A.T. 175–177 (2001) 521
Pataro, L.L., see Danilov, I. 175–177 (2001) 782
Paumier, E., see Benyagoub, A. 175–177 (2001) 417
Peřina, V., see Hnatowicz, V. 175–177 (2001) 437
Peeva, A., P.F.P. Fichtner, M. Behar, R. Koegler and W. Skorupa, Helium implantation induced metal gettering in silicon at half of the projected ion range 175–177 (2001) 176
Peeva, A., see da Silva, D.L. 175–177 (2001) 335
Peeva, A., see Kögler, R. 175–177 (2001) 340
Pereira, A.S., see Soares, S.R.S. 175–177 (2001) 474
Persson, L., see Ecker, K.H. 175–177 (2001) 797
Péter, Á., see Kling, A. 175–177 (2001) 331
Peters, A.M., X.M. He, M. Trkula and M. Nastasi, Annealing of chromium oxycarbide coatings deposited by plasma immersion ion processing (PIIP) for aluminum die casting 175–177 (2001) 599
Petkov, M., see Puglisi, O. 175–177 (2001) 605
Petravic, M., see Stritzker, B. 175–177 (2001) 154
Piekoszewski, J., see Werner, Z. 175–177 (2001) 767
Pipeleers, B., see Vantomme, A. 175–177 (2001) 148
Pipeleers, B., see Hogg, S.M. 175–177 (2001) 585
Pizzini, S., see Devolder, T. 175–177 (2001) 375
Polman, A., see van Dillen, T. 175–177 (2001) 350
Popovici, D., see Bolduc, M. 175–177 (2001) 458
Prawer, S., see Orwa, J.O. 175–177 (2001) 554
Prawer, S., see Jamieson, D.N. 175–177 (2001) 744
Preiß, G., see Wolf, G.K. 175–177 (2001) 756
Priolo, F., see Franzò, G. 175–177 (2001) 140
Prokert, F., see Werner, Z. 175–177 (2001) 767
Puglisi, O., see Compagnini, G. 175–177 (2001) 559
Puglisi, O., M.E. Fragalà, K.G. Lynn, M. Petkov, M. Weber, A. Somoza, A. Dupasquier and F. Quasso, Study of ion beam induced depolymerization using positron annihilation techniques 175–177 (2001) 605

Qadri, S.B., see Molnar, B. 175–177 (2001) 305
Qadri, S.B., see Schiestel, S. 175–177 (2001) 314

Qian, C., B. Terreault and S.C. Gujrathi, Layer splitting in Si by H + He ion co-implantation: Channeling effect limitation at low energy 175–177 (2001) 711
Quasso, F., see Puglisi, O. 175–177 (2001) 605

Radtke, C., see Krug, C. 175–177 (2001) 705
Radtke, M., see Added, N. 175–177 (2001) 787
Rafferty, C.S., see Kalyanaraman, R. 175–177 (2001) 182
Rangel, E.C., N.C. da Cruz, M.H. Tabacniks and C.M. Lepienski, The effect of N^+ ion energy on the properties of ion bombarded plasma polymer films 175–177 (2001) 594
Rangel, E.C., see da Cruz, N.C. 175–177 (2001) 721
Raudino, A., see Compagnini, G. 175–177 (2001) 559
Ravelosona, D., see Devolder, T. 175–177 (2001) 375
Rehn, L.E., see Daulton, T.L. 175–177 (2001) 12
Rehn, L.E., see Birtcher, R.C. 175–177 (2001) 40
Reinoso, M.E., see Huck, H. 175–177 (2001) 772
Reuther, H., see Beloto, A.F. 175–177 (2001) 224
Reuther, H., see Abramof, E. 175–177 (2001) 229
Reuther, H., see Ueda, M. 175–177 (2001) 715
Ridgway, M.C., C.J. Glover, I.D. Desnica-Frankovic, K. Furic, K.M. Yu, G.J. Foran, C. Clerc, J.L. Hansen and A. Nylandsted Larsen, Implantation-induced disorder in *amorphous* Ge: Production and relaxation 175–177 (2001) 21
Ridgway, M.C., see Glover, C.J. 175–177 (2001) 51
Ridgway, M.C., C.J. Glover, K.M. Yu, G.J. Foran, T.W. Lee, Y. Moon and E. Yoon, Structural characterisation of amorphised compound semiconductors 175–177 (2001) 280
Rizzuto, M.A., see Added, N. 175–177 (2001) 787
Robertson, I.M., see Jenčič, I. 175–177 (2001) 197
Rodríguez-Fernández, L., see Cheang-Wong, J.C. 175–177 (2001) 490
Rodríguez-Fernández, L., see Oliver, A. 175–177 (2001) 495
Roiz, J., see Cheang-Wong, J.C. 175–177 (2001) 490
Roiz, J., see Oliver, A. 175–177 (2001) 495
Roorda, S., see Tchebotareva, A.L. 175–177 (2001) 187
Roorda, S., see Héliou, R. 175–177 (2001) 268
Rybka, V., see Hnatowicz, V. 175–177 (2001) 437

Sada, C., see Battaglin, G. 175–177 (2001) 410
Saito, R., see Kimura, T. 175–177 (2001) 286
Salgado, T.D.M., see Krug, C. 175–177 (2001) 694
Samoc, M., see Dowd, A. 175–177 (2001) 637
Sangregorio, C., see de Julián Fernández, C. 175–177 (2001) 479
Sarwe, E.-L., see Zhang, Y. 175–177 (2001) 737
Sataka, M., see Matsunami, N. 175–177 (2001) 56
Schiestel, S., S.B. Qadri, C.A. Carosella, G.K. Hubler and D. Knies, The control of gold nanocluster sizes and volume fraction in dielectric thin films via ion-beam assisted deposition 175–177 (2001) 314
Schiwietz, G., E. Luderer, G. Xiao and P.L. Grande, Energy dissipation of fast heavy ions in matter 175–177 (2001) 1
Schiwietz, G. and P.L. Grande, Improved charge-state formulas 175–177 (2001) 125
Schmidt, B., see Müller, T. 175–177 (2001) 468
Schrempel, F., see Wesch, W. 175–177 (2001) 88
Schwartz, K., see Boccanfuso, M. 175–177 (2001) 590
Sealy, B.J., see Gwilliam, R.M. 175–177 (2001) 62
Senna, J.R., see Beloto, A.F. 175–177 (2001) 224
Serbena, F.C., see Foerster, C.E. 175–177 (2001) 511
Serbena, F.C., see Lepienski, C.M. 175–177 (2001) 668
Serbena, F.C., see Lopes, J.M.J. 175–177 (2001) 673
Shannon, J.M., see Kench, P.J. 175–177 (2001) 678
Shao, G., see Milosavljevic, M. 175–177 (2001) 309
Shao, G., see Kench, P.J. 175–177 (2001) 678
Silva, S.R.P., see Kench, P.J. 175–177 (2001) 678
Simão, R.A., see Castro Vidaurre, E.F. 175–177 (2001) 732

Simpson, P.J., see Lourenco, M.A. ... 175–177 (2001) 300
Skorupa, W., see Peeva, A. ... 175–177 (2001) 176
Skorupa, W., see da Silva, D.L. ... 175–177 (2001) 335
Skorupa, W., see Kögler, R. ... 175–177 (2001) 340
Snoeks, E., see van Dillen, T. ... 175–177 (2001) 350
Soares, J.C., see Alves, E. ... 175–177 (2001) 241
Soares, J.C., see Kling, A. ... 175–177 (2001) 331
Soares, J.C., see Kling, A. ... 175–177 (2001) 394
Soares, S.R.S., N.M. Balzaretti, R.P. Livi, A.S. Pereira and J.A.H. da Jornada, High pressure annealing of defects induced by ion implantation on graphite ... 175–177 (2001) 474
Somoza, A., see Puglisi, O. ... 175–177 (2001) 605
Song, M., see Mitsuishi, K. ... 175–177 (2001) 74
Spinella, C., see Franzò, G. ... 175–177 (2001) 140
Stanisławski, J., see Werner, Z. ... 175–177 (2001) 767
Stedile, F.C., see Krug, C. ... 175–177 (2001) 694
Stedile, F.C., see Krug, C. ... 175–177 (2001) 705
Stedile, F.C., see da Rosa, E.B.O. ... 175–177 (2001) 762
Stonert, A., A. Turos, L. Nowicki, B. Breeger, E. Wendler and W. Wesch, Compositional dependence of defect mobility and damage buildup in $Al_xGa_{1-x}As$ ... 175–177 (2001) 219
Stritzker, B., M. Petravic, J. Wong-Leung and J.S. Williams, Efficiency of dislocations and cavities for gettering of Cu and Fe in silicon ... 175–177 (2001) 154
Stritzker, B., R.G. Elliman and J. Zou, Self-ion-induced swelling of germanium ... 175–177 (2001) 193
Stritzker, B., see Lindner, J.K.N. ... 175–177 (2001) 324
Strohaecker, T.R., see Javorsky, C.S. ... 175–177 (2001) 726
Sudowe, R., P. Vater, R. Brandt, J. Vetter and W. Ensinger, Filters with <100 nm radius pores for gas separation formed by high-energy ion irradiation of polymers ... 175–177 (2001) 564
Suyama, N., see Taniguchi, S. ... 175–177 (2001) 647
Suzuki, Y., see Kurotobi, K. ... 175–177 (2001) 791
Švorčík, V., see Hnatowicz, V. ... 175–177 (2001) 437
Swart, M., see Vantomme, A. ... 175–177 (2001) 148
Swart, M., see Hogg, S.M. ... 175–177 (2001) 585
Szymczyk, W., see Werner, Z. ... 175–177 (2001) 767

Tabacknics, M.H., see da Cruz, N.C. ... 175–177 (2001) 721
Tabacniks, M., see Added, N. ... 175–177 (2001) 787
Tabacniks, M.H., see Rangel, E.C. ... 175–177 (2001) 594
Takeda, Y., see Bandourko, V. ... 175–177 (2001) 68
Takeda, Y., see Amekura, H. ... 175–177 (2001) 345
Takeda, Y., see Kishimoto, N. ... 175–177 (2001) 426
Takeda, Y., N. Umeda, V.T. Gritsyna and N. Kishimoto, Optical transient resonance of copper nanoparticle composites synthesized by negative ion implantation ... 175–177 (2001) 463
Takeda, Y., see Okubo, N. ... 175–177 (2001) 663
Taniguchi, S., A. Kitahara, S. Wakayama, E. Eriguchi and N. Suyama, Characterization of mechanical properties and microstructure of high-energy dual ion implanted metals ... 175–177 (2001) 647
Tazawa, M., see Ikeyama, M. ... 175–177 (2001) 652
Tchebotareva, A.L., J.L. Brebner, S. Roorda and C.W. White, Properties of InAs nanocrystals in silicon formed by sequential ion implantation ... 175–177 (2001) 187
Teixeira, S.R., see Borges, J.F.M. ... 175–177 (2001) 485
Tentardini, E.K., see Blando, E. ... 175–177 (2001) 620
Tentardini, E.K., E. Blando and R. Hübler, TiN structural modifications induced by bias voltage in a new dynamic controlled magnetron sputtering apparatus ... 175–177 (2001) 626
Terashima, K., see Toida, H. ... 175–177 (2001) 532
Terashima, K., see Aono, K. ... 175–177 (2001) 580
Terreault, B., see Bolduc, M. ... 175–177 (2001) 458
Terreault, B., see Qian, C. ... 175–177 (2001) 711
The ISOLDE collaboration, see Wahl, U. ... 175–177 (2001) 262
Thevuthasan, S., see Weber, W.J. ... 175–177 (2001) 26

Thevuthasan, S., see Jiang, W. . . . 175–177 (2001) 610
Thomae, R.W., see Galonska, M. . . . 175–177 (2001) 658
Thomé, L., see Birtcher, R.C. . . . 175–177 (2001) 40
Thomé, L., see Jagielski, J. . . . 175–177 (2001) 448
Thomé, L., J. Jagielski, A. Gentils and F. Garrido, Lattice location of Cs atoms in cubic ZrO_2 single crystals 175–177 (2001) 453
Thomé, L., see Fradin, J. . . . 175–177 (2001) 516
Thomé, T., see Fradin, J. . . . 175–177 (2001) 516
Toda, H., see Kimura, T. . . . 175–177 (2001) 286
Toida, H., K. Terashima, T. Kobayashi, M. Osada, K. Watanabe and M. Iwaki, Densification of glassy carbon by fluorine ion implantation . . . 175–177 (2001) 532
Toida, H., see Aono, K. . . . 175–177 (2001) 580
Tokumoto, H., see Ogiso, H. . . . 175–177 (2001) 641
Toulemonde, M., see Boccanfuso, M. . . . 175–177 (2001) 590
Trasferetti, B.C., see da Cruz, N.C. . . . 175–177 (2001) 721
Trautmann, C., see Boccanfuso, M. . . . 175–177 (2001) 590
Trinkaus, H., see Holländer, B. . . . 175–177 (2001) 357
Trkula, M., see Peters, A.M. . . . 175–177 (2001) 599
Tsakiropoulos, P., see Kench, P.J. . . . 175–177 (2001) 678
Tsubouchi, N., see Kinomura, A. . . . 175–177 (2001) 319
Turos, A., see Stonert, A. . . . 175–177 (2001) 219

Ueda, M., see Beloto, A.F. . . . 175–177 (2001) 224
Ueda, M., see Abramof, E. . . . 175–177 (2001) 229
Ueda, M., H. Reuther, R. Gunzel, A.F. Beloto, E. Abramof and L.A. Berni, High dose nitrogen and carbon shallow implantation in Si by plasma immersion ion implantation . . . 175–177 (2001) 715
Umeda, N., see Amekura, H. . . . 175–177 (2001) 345
Umeda, N., see Kishimoto, N. . . . 175–177 (2001) 426
Umeda, N., see Takeda, Y. . . . 175–177 (2001) 463

van Blaaderen, A., see van Dillen, T. . . . 175–177 (2001) 350
van Dillen, T., E. Snoeks, W. Fukarek, C.M. van Kats, K.P. Velikov, A. van Blaaderen and A. Polman, Anisotropic deformation of colloidal particles under MeV ion irradiation . . . 175–177 (2001) 350
van Kats, C.M., see van Dillen, T. . . . 175–177 (2001) 350
Vantomme, A., S.M. Hogg, M.F. Wu, B. Pipeleers, M. Swart, S. Goodman, D. Auret, K. Iakoubovskii, G.J. Adriaenssens, K. Jacobs and I. Moerman, Suppression of rare-earth implantation-induced damage in GaN . . . 175–177 (2001) 148
Vantomme, A., see Wahl, U. . . . 175–177 (2001) 262
Vantomme, A., see Hogg, S.M. . . . 175–177 (2001) 585
Vasconcellos, M.A.Z., see Javorsky, C.S. . . . 175–177 (2001) 726
Vater, P., see Sudowe, R. . . . 175–177 (2001) 564
Velikov, K.P., see van Dillen, T. . . . 175–177 (2001) 350
Verda, R., see Höchbauer, T. . . . 175–177 (2001) 169
Vetter, J., see Sudowe, R. . . . 175–177 (2001) 564
Vieira, A., see Barradas, N.P. . . . 175–177 (2001) 108
Vishnyakov, V.M., see Donnelly, S.E. . . . 175–177 (2001) 132
Vogel, J., see Devolder, T. . . . 175–177 (2001) 375
Volz, K., Ch. Klatt and W. Ensinger, Heteroepitaxial SiC films grown in Si by CH_4 plasma immersion ion implantation: Conditions and mechanisms of their formation . . . 175–177 (2001) 569
Volz, K., see Lensch, O. . . . 175–177 (2001) 575
Volz, K., see Galonska, M. . . . 175–177 (2001) 658

Waerenborgh, J.C., see Alves, E. . . . 175–177 (2001) 241
Wahl, U., A. Vantomme, G. Langouche, J.P. Araújo and The ISOLDE collaboration, Emission channeling studies of implanted ^{167m}Er in InP . . . 175–177 (2001) 262
Wakaya, F., see Hada, T. . . . 175–177 (2001) 751
Wakayama, S., see Taniguchi, S. . . . 175–177 (2001) 647
Wang, L.M., see Nakao, S. . . . 175–177 (2001) 202

Wang, L.M., see Wang, S.X. ... 175–177 (2001) 615
Wang, S.X., see Nakao, S. ... 175–177 (2001) 202
Wang, S.X., L.M. Wang and R.C. Ewing, Ion irradiation-induced amorphization of two GeO_2 polymorphs ... 175–177 (2001) 615
Watanabe, K., see Toida, H. ... 175–177 (2001) 532
Wätjen, U., see Ecker, K.H. ... 175–177 (2001) 797
Weber, B. and K. Gärtner, The role of point defects in ion beam induced crystallization of silicon investigated by molecular dynamics simulations ... 175–177 (2001) 119
Weber, M., see Puglisi, O. ... 175–177 (2001) 605
Weber, W.J., W. Jiang and S. Thevuthasan, Accumulation, dynamic annealing and thermal recovery of ion-beam-induced disorder in silicon carbide ... 175–177 (2001) 26
Weber, W.J., see Jiang, W. ... 175–177 (2001) 610
Wendler, E., B. Breeger and W. Wesch, Anomalous damaging behaviour of AlAs during ion implantation at 15 K ... 175–177 (2001) 78
Wendler, E., B. Breeger and W. Wesch, In situ investigation of AlAs/GaAs interfaces during ion implantation at 15 K ... 175–177 (2001) 83
Wendler, E., see Stonert, A. ... 175–177 (2001) 219
Wendler, E., see Wesch, W. ... 175–177 (2001) 257
Wenzel, S., see Lindner, J.K.N. ... 175–177 (2001) 324
Werner, P., see Kögler, R. ... 175–177 (2001) 340
Werner, Z., J. Piekoszewski, A. Barcz, R. Grözschel, F. Prokert, J. Stanisławski and W. Szymczyk, Alloying of Pd into Ti by pulsed plasma beams ... 175–177 (2001) 767
Wesch, W., see Wendler, E. ... 175–177 (2001) 78
Wesch, W., see Wendler, E. ... 175–177 (2001) 83
Wesch, W., Th. Opfermann, F. Schrempel and Th. Höche, Track formation in $KTiOPO_4$ by MeV implantation of light ions ... 175–177 (2001) 88
Wesch, W., see Stonert, A. ... 175–177 (2001) 219
Wesch, W., E. Wendler and N. Dharmarasu, Effects of the ion energy on damage production in MeV ion-implanted GaAs ... 175–177 (2001) 257
White, C.W., see Tchebotareva, A.L. ... 175–177 (2001) 187
Whitlow, H.J., see Zhang, Y. ... 175–177 (2001) 737
Williams, J.S., see Stritzker, B. ... 175–177 (2001) 154
Williams, J.S., see Kucheyev, S.O. ... 175–177 (2001) 214
Wolf, G.K., see Heyden, D. ... 175–177 (2001) 403
Wolf, G.K., G. Preiß, R. Münz and L. Guzman, Large area IBAD deposition of Zn-alloys in the coil coating mode ... 175–177 (2001) 756
Wong-Leung, J., see Stritzker, B. ... 175–177 (2001) 154
Wong-Leung, J., see Liu, A.C.Y. ... 175–177 (2001) 164
Wright, A.F., see Barbour, J.C. ... 175–177 (2001) 382
Wu, M.F., see Vantomme, A. ... 175–177 (2001) 148
Wu, M.F., see Hogg, S.M. ... 175–177 (2001) 585

Xiao, G., see Schiwietz, G. ... 175–177 (2001) 1

Yamada, I., see Birtcher, R.C. ... 175–177 (2001) 36
Yamanaka, K., see Ogiso, H. ... 175–177 (2001) 641
Yanagisawa, J., see Hada, T. ... 175–177 (2001) 751
Yasuda, H., see Mitsuishi, K. ... 175–177 (2001) 74
Yokota, Y., see Heck, C. ... 175–177 (2001) 296
Yoon, E., see Ridgway, M.C. ... 175–177 (2001) 280
Yoon, M., see Kalyanaraman, R. ... 175–177 (2001) 182
Yu, K.M., see Ridgway, M.C. ... 175–177 (2001) 21
Yu, K.M., see Ridgway, M.C. ... 175–177 (2001) 280
Yuba, Y., see Hada, T. ... 175–177 (2001) 751

Zawislak, F., see Kling, A. ... 175–177 (2001) 331
Zawislak, F., see Kling, A. ... 175–177 (2001) 394
Zawislak, F.C., see Feldmann, G. ... 175–177 (2001) 432
Zawislak, F.C., see Lepienski, C.M. ... 175–177 (2001) 668
Zawislak, F.C., see Lopes, J.M.J. ... 175–177 (2001) 673

Zhang, T., see Zhang, Y. 175–177 (2001) 737
Zhang, Y., T. Zhang, D.-T. Lu, I.A. Maximov, E.-L. Sarwe, M. Graczyk and H.J. Whitlow, Annealing behaviour of foreign atom incorporated Co-silicides formed by MEVVA implantation into SiO_2/Si and Si_3N_4/Si structures 175–177 (2001) 737
Zhao, J.P., see Okubo, N. 175–177 (2001) 663
Zheng, Y., see Höchbauer, T. 175–177 (2001) 169
Zou, J., see Stritzker, B. 175–177 (2001) 193
Zou, J., see Kucheyev, S.O. 175–177 (2001) 214